TPS720-Q1

具有偏置引脚的 350mA、超低 V_{IN}、RF 低压降线性稳压器

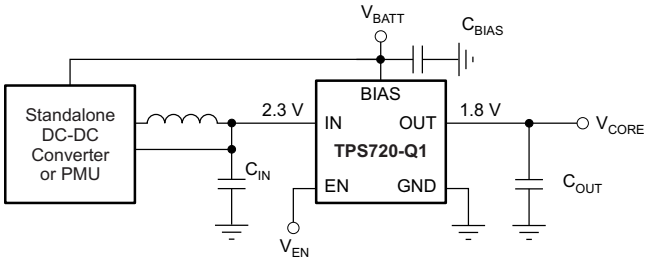
1 特性

- 适用于汽车电子 应用
- 具有符合 AEC-Q100 标准的下列结果：
  - 器件温度 1 级：-40℃ 至 +125℃ 的环境运行温度范围
  - 器件人体放电模式 (HBM) 静电放电 (ESD) 分类等级 H2
  - 器件组件充电模式 (CDM) ESD 分类等级 C6
- 输入电压范围：1.1V 至 4.5V
- 输出电压范围：0.9V 至 3.6V
- 高性能 LDO：350mA
- 低静态电流：38μA
- 绝佳的负载瞬态响应：
  ±15mV（当 1μs 内 I_{LOAD} = 0mA 跳至 350 mA 时）
- 低噪声：48μV_{RMS}（10Hz 至 100kHz）
- 80dB V_{IN} PSRR（10Hz 至 10kHz）
- 70dB V_{BIAS} PSRR (10Hz 至 10kHz)
- 快速启动时间：140μs
- 内置软启动，单调 V_{OUT} 升高并且启动电流限制在 100mA + I_{LOAD}
- 过流和热保护
- 低压降：110mV（当 I_{LOAD} = 350mA 时）
- 与 2.2μF 输出电容一起工作时保持稳定
- 封装：2.00mm × 2.00mm、6 引脚 WSON

2 应用

- 摄像机模块
- 平板显示 (FPD) 链路电源
- 车用信息娱乐系统
- USB 网络集线器 (HUB) 电源

简化电路原理图



3 说明

TPS720-Q1 系列双轨、低压降线性稳压器 (LDO) 具有出色的交流性能（PSRR，负载和线路瞬态响应），静态流耗非常低，低至 38μA。

为 LDO 控制电路供电的 V_{BIAS} 轨消耗极低的电流（与 LDO 静态电流差不多），并且可以连接至任何超过输出电压 1.4V 及以上的电源。主要电源路径为 V_{IN}，且可低于 V_{BIAS}；此路径可低至 V_{OUT} + V_{DO}，有助于提高许多功耗敏感型 应用解决方案的效率。例如，V_{IN} 可作为高效的直流 - 直流降压稳压器的输出。

TPS720-Q1 支持一种新特性，当 IN 引脚保持悬空时，LDO 的输出稳定在轻负载以下。这种情况下的轻负载驱动电流来源于 V_{BIAS}。此特性对于 节能应用特别有效， 在这些应用中，禁止直流-直流转换器连接至 IN 引脚，但仍需要 LDO 将电压稳定至轻负载。

TPS720-Q1 与陶瓷电容器搭配使用时可保持稳定，并且该器件使用先进的 BICMOS 制造工艺，能够在 350mA 输出负载电流时产生仅 110mV 的压降。TPS720-Q1 搭配 2.2μF 输出电容时，可实现 V_{OUT} 单调升高（过冲限制为 3%）的同时 V_{IN} 浪涌电流限制为 100mA + I_{LOAD}。

TPS720-Q1 使用一个高精度电压基准和反馈环路来实现负载、线路、过程和温度变化范围上 2% 的总精度。TPS720-Q1 采用 6 引脚 WSON 封装。该系列器件的额定工作温度范围为 T_J = –40°C 至 +125°C。

器件信息(1)

器件型号	封装	封装尺寸（标称值）
TPS720-Q1	WSON (6)	2.00mm x 2.00mm

(1) 要了解所有可用封装，请见数据表末尾的可订购产品附录。

目录

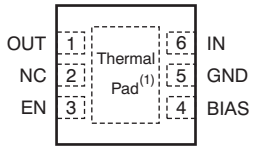
4 修订历史记录

Changes from Original (February 2016) to Revision A **Page**

- 已更改 *特性*部分中的输出电压范围要点从“0.9V 至 3.0V”更改为“0.9V 至 3.6V” ... 1
- Changed maximum value of "output voltage" parameter from 3.0 V to 3.6 V in *Recommended Operating Conditions* table ... 4
- Reformatted *Thermal Information* table note ... 4
- Changed maximum value of *output voltage* parameter from 3.0 V to 3.6 V in *Electrical Characteristics* table ... 5
- 已更改 *器件命名规则*部分 ... 18
- 已更改 *相关文档*部分的格式 ... 18
- 已添加 *接收文档更新通知*部分 ... 18

5 Pin Configuration and Functions

DRV Package
6-Pin WSON With Exposed Thermal Pad
Top View



(1) TI recommends connecting the WSON (DRV) package thermal pad to ground.

Pin Functions

PIN		I/O	DESCRIPTION
NAME	NO.		
OUT	1	O	Output pin. A 2.2-µF ceramic capacitor is connected from this pin to ground for stability and to provide load transients; see *Input and Output Capacitor Requirements*
NC	2	—	No connection.
EN	3	I	Enable pin. A logic high signal on this pin turns the device on and regulates the voltage from IN to OUT. A logic low on this pin turns the device off.
BIAS	4	I	Bias supply pin. For better transient performance, TI recommends bypassing this input with a ceramic capacitor to ground; see *Input and Output Capacitor Requirements*
GND	5	—	Ground pin.
IN	6	I	Input pin. This pin can be a maximum of 4.5 V; V_{IN} must not exceed V_{BIAS}. Bypass this input with a ceramic capacitor to ground; see *Input and Output Capacitor Requirements*.

6 Specifications

6.1 Absolute Maximum Ratings

at T_J = –40°C to +125°C (unless otherwise noted); all voltages are with respect to GND(1)

		MIN	MAX	UNIT
V_{IN}(2)	Input voltage (steady-state)	–0.3	V_{BIAS} or 5(3)	V
V_{IN_PEAK}(4)	Peak transient input		5.5	V
V_{BIAS}	Bias voltage	–0.3	6	V
V_{EN}	Enable voltage	–0.3	6	V
V_{OUT}	Output voltage	–0.3	5	V
I_{OUT}	Peak output current	Internally limited		
	Output short-circuit duration	Indefinite		
P_{DISS}	Total continuous power dissipation	See *Thermal Information*		
T_J	Operating junction temperature	–55	125	°C
T_{stg}	Storage temperature	–55	150	°C

(1) Stresses beyond those listed under *Absolute Maximum Ratings* may cause permanent damage to the device. These are stress ratings only, which do not imply functional operation of the device at these or any other conditions beyond those indicated under *Recommended Operating Conditions*. Exposure to absolute-maximum-rated conditions for extended periods may affect device reliability.
(2) To ensure proper device operation, V_{IN} must be less than or equal to V_{BIAS} under all conditions.
(3) Whichever is less.
(4) For durations no longer than 1 ms each, for a total of no more than 1000 occurrences over the lifetime of the device.

6.2 ESD Ratings

			VALUE	UNIT
$V_{(ESD)}$	Electrostatic discharge	Human-body model (HBM), per ANSI/ESDA/JEDEC JS-001 (1)	±2000	V
		Charged-device model (CDM), per JEDEC specification JESD22-C101 (2)	±500	
		Machine model (MM)	±100	

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process.
(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process.

6.3 Recommended Operating Conditions

over operating junction temperature range (unless otherwise noted).

		MIN	NOM	MAX	UNIT
V_{IN}	Input voltage (steady-state)	1.1		V_{BIAS} or 4.5 (1)	V
V_{BIAS}	Bias voltage	2.6 or V_{OUT} + 1.4 (2)		5.5	V
V_{OUT}	Output voltage	0.9		3.6	V
I_{OUT}	Peak output current	0		350	mA
V_{EN}	Enable voltage	0		5.5	V
C_{IN}	Input capacitance		1		µF
C_{BIAS}	Bias capacitance		0.1		µF
C_{OUT} (3)	Output capacitance	2.2			µF

(1) Whichever is less.
(2) Whichever is greater.
(3) Maximum ESR must be less than 250 mΩ.

6.4 Thermal Information

THERMAL METRIC (1)		TPS720-Q1 DRV (WSON) 6 PINS	UNIT
$R_{\theta JA}$	Junction-to-ambient thermal resistance	66.5	°C/W
$R_{\theta JC(top)}$	Junction-to-case (top) thermal resistance	86.2	°C/W
$R_{\theta JB}$	Junction-to-board thermal resistance	36.1	°C/W
ψ_{JT}	Junction-to-top characterization parameter	1.7	°C/W
ψ_{JB}	Junction-to-board characterization parameter	36.6	°C/W
$R_{\theta JC(bot)}$	Junction-to-case (bottom) thermal resistance	7.4	°C/W

(1) For more information about traditional and new thermal metrics, see *Semiconductor and IC Package Thermal Metrics* (SPRA953).

6.5 Electrical Characteristics

over operating temperature range (T_J = –40°C to +125°C), V_{BIAS} = (V_{OUT} + 1.4 V) or 2.6 V (whichever is greater), $V_{IN} \geq V_{OUT}$ + 0.5 V, I_{OUT} = 1 mA, V_{EN} = 1.1 V, and C_{OUT} = 2.2 µF (unless otherwise noted); typical values are at T_J = 25°C

PARAMETER			TEST CONDITIONS		MIN	TYP	MAX	UNIT
V_{IN}	Input voltage				1.1(1)		V_{BIAS} or 4.5(2)	V
V_{BIAS}	Bias voltage				2.6		5.5	V
V_{OUT}(3)	Output voltage(4)				0.9		3.6	V
	Output accuracy	Over V_{BIAS}, V_{IN}, I_{OUT}, T_J = –40°C to +125°C	V_{OUT} + 1.4 V ≤ V_{BIAS} ≤ 5.5 V, V_{OUT} + 0.5 V ≤ V_{IN} ≤ 4.5 V, 0 mA ≤ I_{OUT} ≤ 350 mA		–2%		2%	
		Over V_{BIAS}, V_{IN}, I_{OUT}, T_J = –40°C to +125°C	V_{OUT} + 1.4 V ≤ V_{BIAS} ≤ 5.5 V, V_{OUT} + 0.5 V ≤ V_{IN} ≤ 4.5 V, 0 mA ≤ I_{OUT} ≤ 350 mA, V_{OUT} < 1.2 V		–25		25	mV
		V_{IN} floating	V_{OUT} + 1.4 V ≤ V_{BIAS} ≤ 5.5 V, 0 µA ≤ I_{OUT} ≤ 500 µA			±1%		
$\Delta V_{OUT}/\Delta V_{IN}$	V_{IN} line regulation		V_{IN} = (V_{OUT} + 0.5 V) to 4.5 V, I_{OUT} = 1 mA			16		µV/V
$\Delta V_{OUT}/\Delta V_{BIAS}$	V_{BIAS} line regulation		V_{BIAS} = (V_{OUT} + 1.4 V) or 2.6 V (whichever is greater) to 5.5 V, I_{OUT} = 1 mA			16		µV/V
	V_{IN} line transient		ΔV_{IN} = 400 mV, t_{RISE} = t_{FALL} = 1 µs			±200		µV
	V_{BIAS} line transient		ΔV_{BIAS} = 600 mV, t_{RISE} = t_{FALL} = 1 µs			±0.8		mV
$\Delta V_{OUT}/\Delta I_{OUT}$	Load regulation		0 mA ≤ I_{OUT} ≤ 350 mA (no load to full load)			–15		µV/mA
	Load transient		0 mA ≤ I_{OUT} ≤ 350 mA, t_{RISE} = t_{FALL} = 1 µs			±15		mV
V_{DO_IN}	V_{IN} dropout voltage(5)		V_{IN} = $V_{OUT(NOM)}$ – 0.1 V, (V_{BIAS} – $V_{OUT(NOM)}$) = 1.4 V, I_{OUT} = 350 mA			110	200	mV
V_{DO_BIAS}	V_{BIAS} dropout voltage(6)		V_{IN} = $V_{OUT(NOM)}$ + 0.3 V, I_{OUT} = 350 mA			1.09	1.4	V
I_{CL}	Output current limit		V_{OUT} = 0.9 × $V_{OUT(NOM)}$		420	600	800	mA
I_{GND}	Ground pin current		I_{OUT} = 100 µA			38		µA
			I_{OUT} = 0 mA to 350 mA			54	80	
I_{SHDN}	Shutdown current (I_{GND})		V_{EN} ≤ 0.4 V			0.5	2.5	µA
PSRR	V_{IN} power-supply rejection ratio		V_{IN} – V_{OUT} ≥ 0.5 V, V_{BIAS} = V_{OUT} + 1.4 V, I_{OUT} = 350 mA	f = 10 Hz		85		dB
				f = 100 Hz		85		
				f = 1 kHz		85		
				f = 10 kHz		80		
				f = 100 kHz		70		
				f = 1 MHz		50		
PSRR	V_{BIAS} power-supply rejection ratio		V_{IN} – V_{OUT} ≥ 0.5 V, V_{BIAS} = V_{OUT} + 1.4 V, I_{OUT} = 350 mA	f = 10 Hz		80		dB
				f = 100 Hz		80		
				f = 1 kHz		75		
				f = 10 kHz		65		
				f = 100 kHz		55		
				f = 1 MHz		35		
V_N	Output noise voltage		Bandwidth = 10 Hz to 100 kHz, V_{BIAS} ≥ 2.6 V, V_{IN} = V_{OUT} + 0.5 V			48		μV_{RMS}
I_{VIN_INRUSH}	Inrush current on V_{IN}		V_{BIAS} = (V_{OUT} +1.4 V) or 2.6 V (whichever is greater), V_{IN} = V_{OUT} + 0.5 V			100 + I_{LOAD}		mA
$V_{EN(HI)}$	Enable pin high (enabled)				1.1			V
$V_{EN(LO)}$	Enable pin low (disabled)				0		0.4	V

(1) Performance specifications are ensured to a minimum V_{IN} = V_{OUT} + 0.5 V.
(2) Whichever is less.
(3) Minimum V_{BIAS} = (V_{OUT} + 1.4 V) or 2.6 V (whichever is greater) and V_{IN} = V_{OUT} + 0.5 V.
(4) V_O nominal value is factory programmable through the on-chip EEPROM.
(5) Measured for devices with $V_{OUT(NOM)} \geq$ 1.2 V.
(6) V_{BIAS} – V_{OUT} with V_{OUT} = $V_{OUT(NOM)}$ – 0.1 V. Measured for devices with $V_{OUT(NOM)} \geq$ 1.8 V.

Electrical Characteristics (continued)

over operating temperature range (T_J = –40°C to +125°C), V_{BIAS} = (V_{OUT} + 1.4 V) or 2.6 V (whichever is greater), $V_{IN} \geq V_{OUT}$ + 0.5 V, I_{OUT} = 1 mA, V_{EN} = 1.1 V, and C_{OUT} = 2.2 μF (unless otherwise noted); typical values are at T_J = 25°C

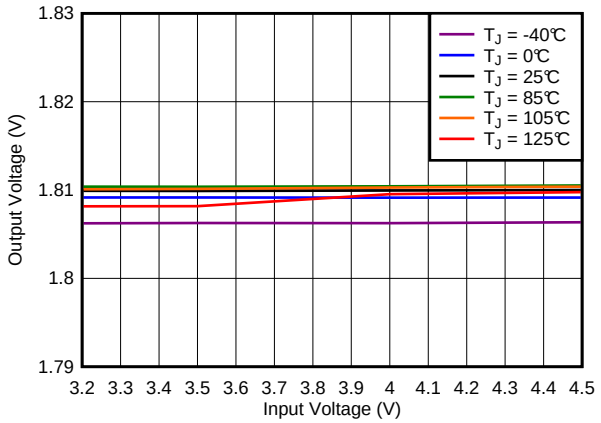
PARAMETER		TEST CONDITIONS	MIN	TYP	MAX	UNIT
I_{EN}	Enable pin current	V_{EN} = 5.5 V, V_{IN} = 4.5 V, V_{BIAS} = 5.5 V			1	μA
UVLO	Undervoltage lockout	V_{BIAS} rising	2.35	2.45	2.59	V
	UVLO hysteresis	V_{BIAS} falling		150		mV
T_{SD}	Thermal shutdown temperature	Shutdown, temperature increasing		160		°C
		Reset, temperature decreasing		140		
T_J	Operating junction temperature		–40		125	°C

6.6 Timing Requirements

			MIN	NOM	MAX	UNIT
t_{STR}	Start-up time	V_{OUT} = 95%, $V_{OUT\ (NOM)}$, I_{OUT} = 350 mA, C_{OUT} = 2.2 μF		140		μs

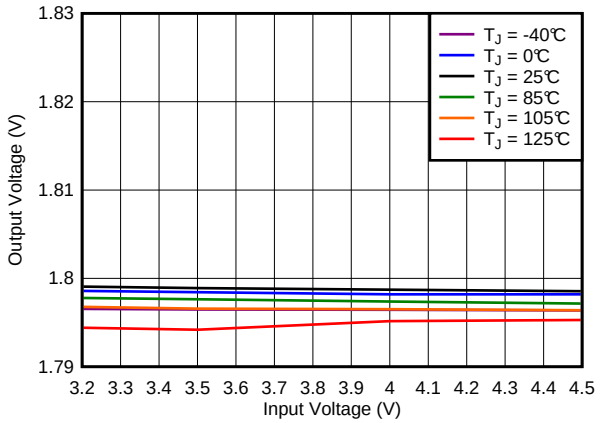
6.7 Typical Characteristics

over operating temperature range (T_J = –40°C to +125°C), V_{BIAS} = (V_{OUT} + 1.4 V) or 2.6 V (whichever is greater), V_{IN} = V_{OUT} + 0.5 V, I_{OUT} = 1 mA, V_{EN} = 1.1 V, and C_{OUT} = 2.2 µF (unless otherwise noted); typical values are at T_J = 25°C



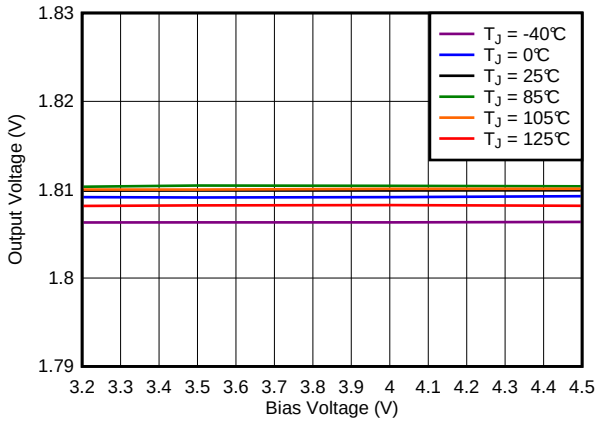
I_{OUT} = 0 mA

Figure 1. V_{IN} Line Regulation (No Load)



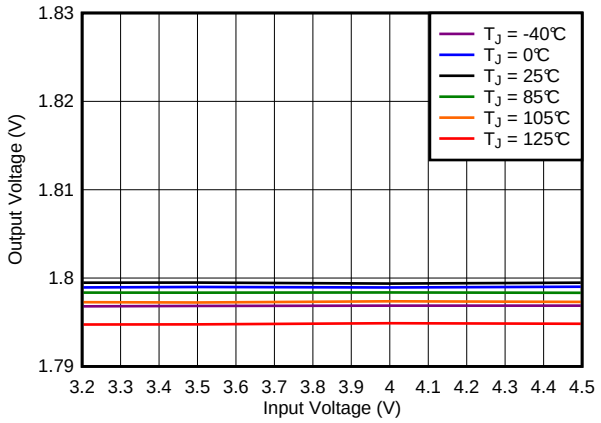
I_{OUT} = 350 mA

Figure 2. V_{IN} Line Regulation (350 mA)



I_{OUT} = 0 mA

Figure 3. V_{BIAS} Line Regulation (No Load)



I_{OUT} = 350 mA

Figure 4. V_{BIAS} Line Regulation (350 mA)

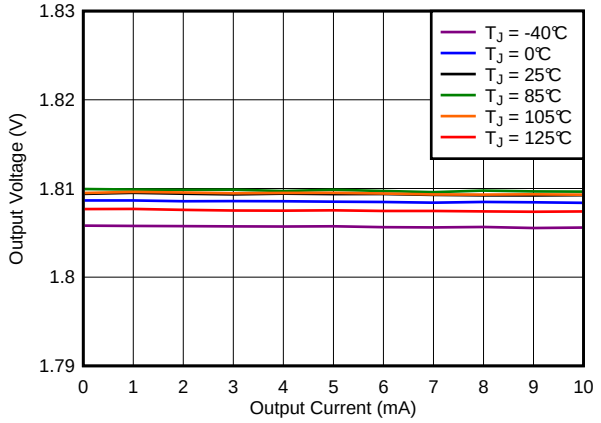


Figure 5. Load Regulation Under Light Loads

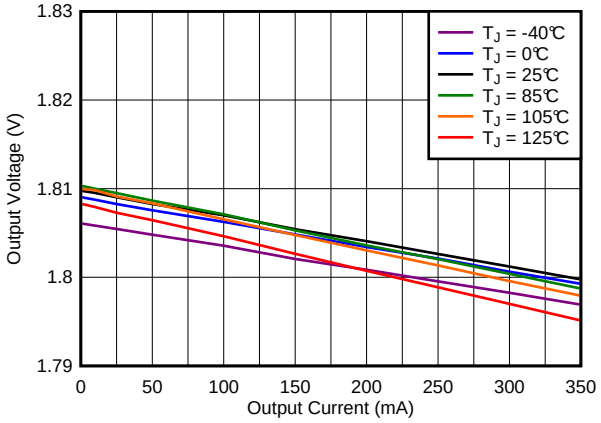


Figure 6. Load Regulation

Typical Characteristics (continued)

over operating temperature range (T_J = –40°C to +125°C), V_{BIAS} = (V_{OUT} + 1.4 V) or 2.6 V (whichever is greater), V_{IN} = V_{OUT} + 0.5 V, I_{OUT} = 1 mA, V_{EN} = 1.1 V, and C_{OUT} = 2.2 µF (unless otherwise noted); typical values are at T_J = 25°C

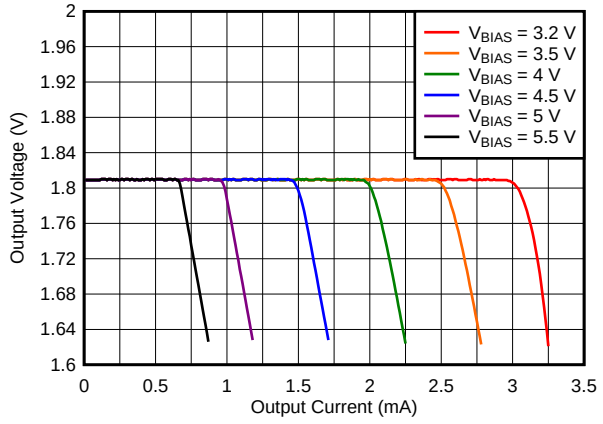


Figure 7. Load Regulation With V_{IN} Floating

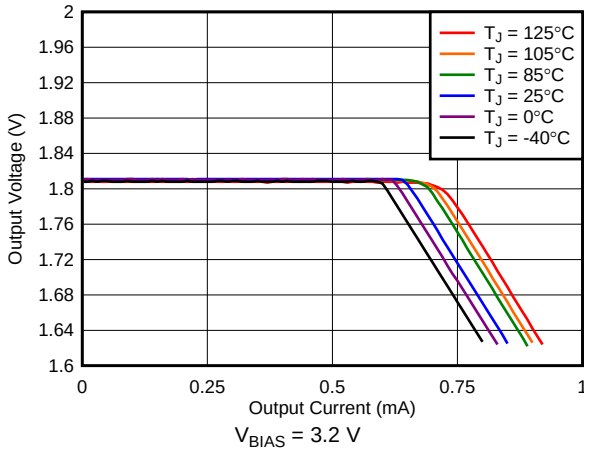


Figure 8. Load Regulation With V_{IN} Floating

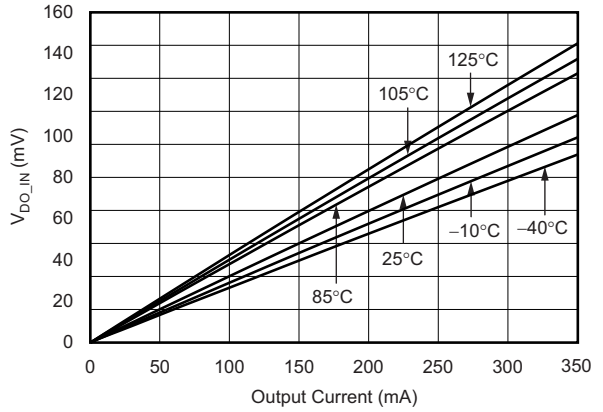


Figure 9. V_{IN} Dropout Voltage vs Output Current

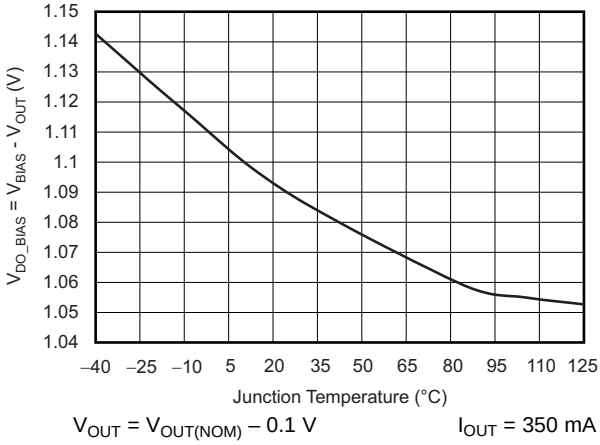


Figure 10. V_{BIAS} Dropout Voltage vs Junction Temperature

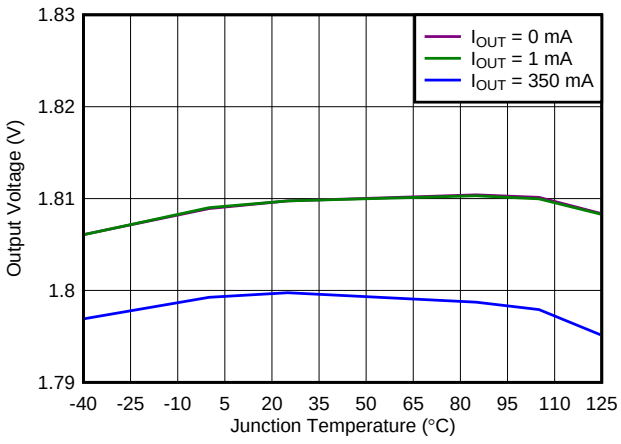


Figure 11. Output Voltage vs Junction Temperature

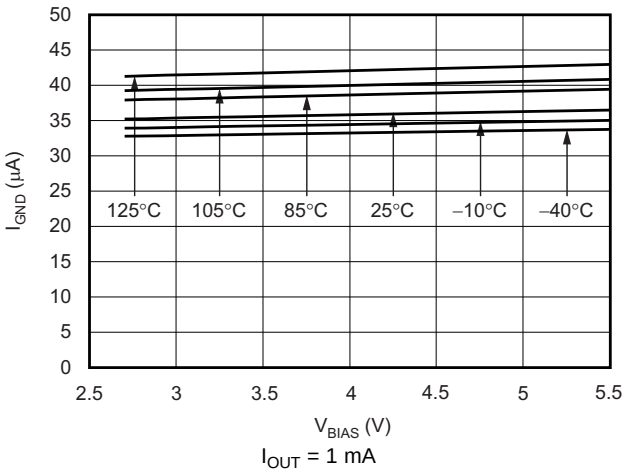


Figure 12. Ground Pin Current vs V_{BIAS} Voltage

Typical Characteristics (continued)

over operating temperature range (T_J = –40°C to +125°C), V_{BIAS} = (V_{OUT} + 1.4 V) or 2.6 V (whichever is greater), V_{IN} = V_{OUT} + 0.5 V, I_{OUT} = 1 mA, V_{EN} = 1.1 V, and C_{OUT} = 2.2 µF (unless otherwise noted); typical values are at T_J = 25°C

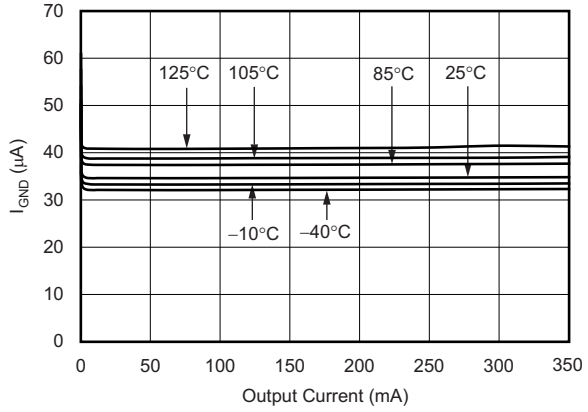


Figure 13. Ground Pin Current vs Output Current

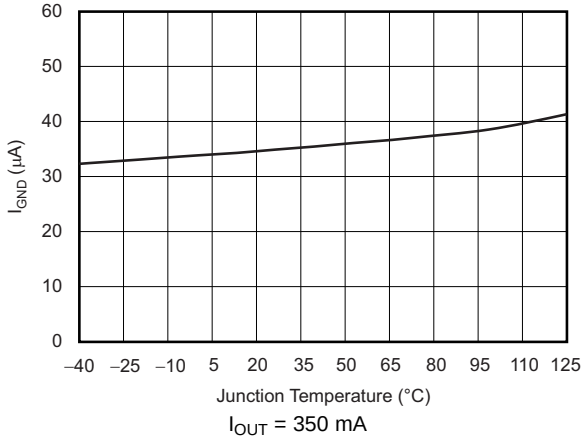


Figure 14. Ground Pin Current vs Junction Temperature

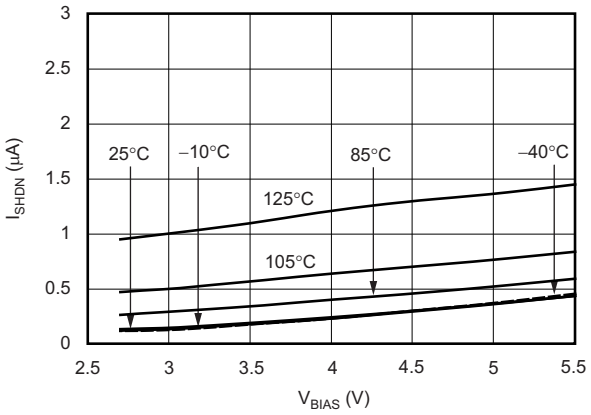


Figure 15. Shutdown Current vs V_{BIAS} Voltage

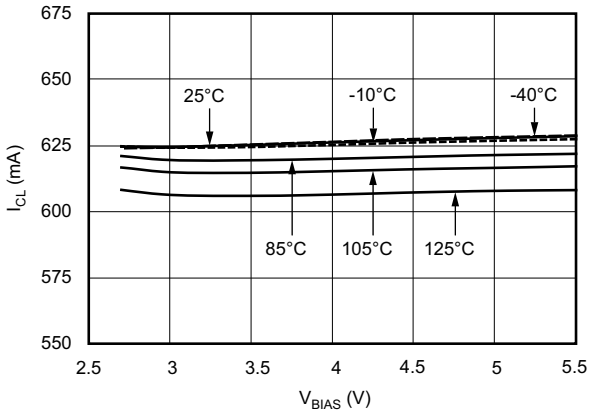


Figure 16. Current Limit vs V_{BIAS} Voltage

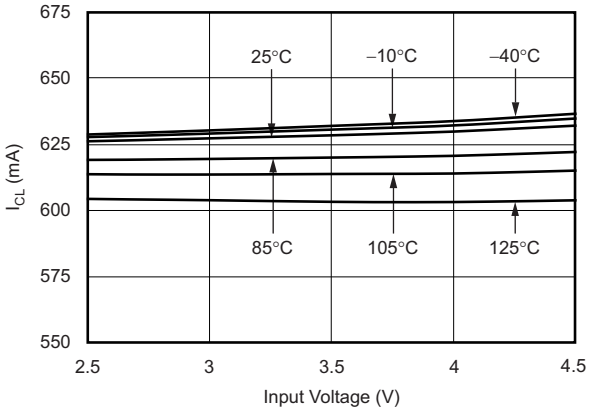


Figure 17. Current Limit vs Input Voltage

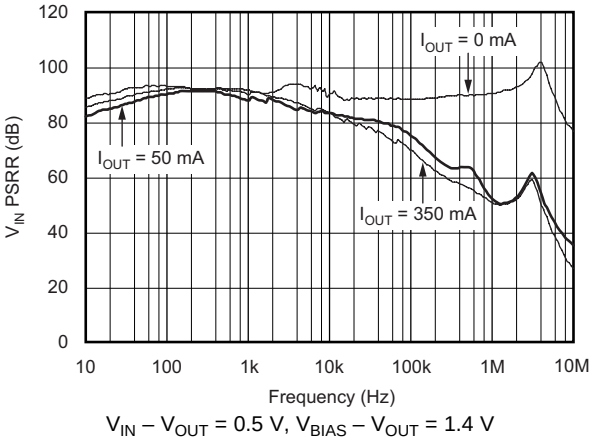
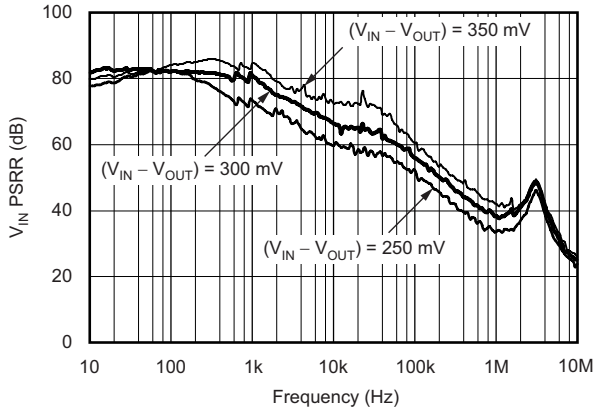


Figure 18. V_{IN} Power-Supply Rejection Ratio vs Frequency

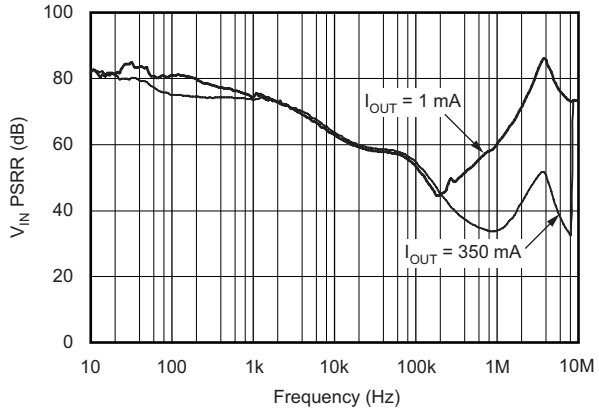
Typical Characteristics (continued)

over operating temperature range (T_J = –40°C to +125°C), V_{BIAS} = (V_{OUT} + 1.4 V) or 2.6 V (whichever is greater), V_{IN} = V_{OUT} + 0.5 V, I_{OUT} = 1 mA, V_{EN} = 1.1 V, and C_{OUT} = 2.2 µF (unless otherwise noted); typical values are at T_J = 25°C



I_{OUT} = 350 mA

Figure 19. V_{IN} Power-Supply Rejection Ratio vs Frequency



V_{IN} – V_{OUT} = 0.5 V V_{BIAS} – V_{OUT} = 1.4 V

Figure 20. V_{BIAS} Power-Supply Rejection Ratio vs Frequency

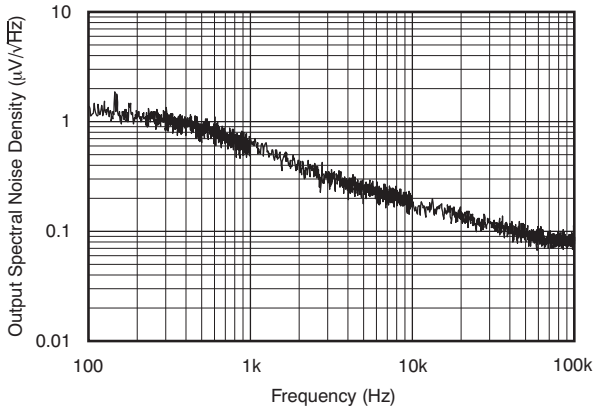
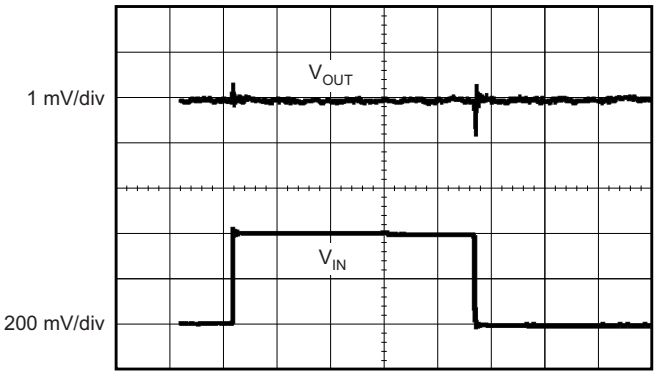
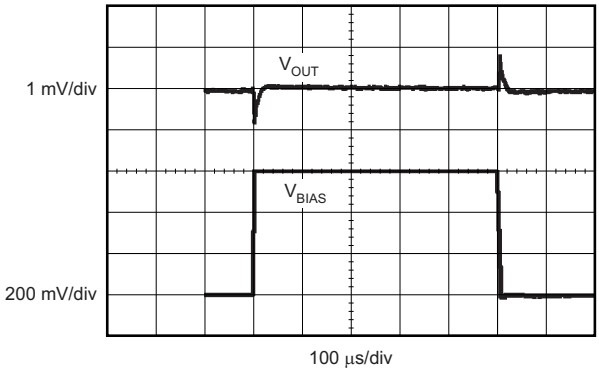


Figure 21. Output Spectral Noise Density vs Frequency



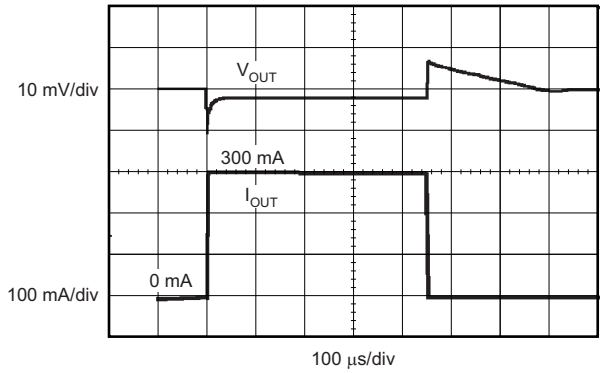
V_{IN} = 2.1 to 2.5 V V_{OUT} = 1.8 V V_{BIAS} = 3.2 V
V_{IN} slew rate = 1 V/µs I_{OUT} = 350 mA

Figure 22. V_{IN} Line Transient Response



V_{IN} = 2.3 V V_{OUT} = 1.8 V V_{BIAS} = 3.2 V to 3.8 V
V_{BIAS} slew rate = 600 m/µs I_{OUT} = 350 mA

Figure 23. V_{BIAS} Line Transient Response



V_{IN} = 2.3 V V_{OUT} = 1.8 V V_{BIAS} = 3.2 V
t_{RISE} = 1 µs

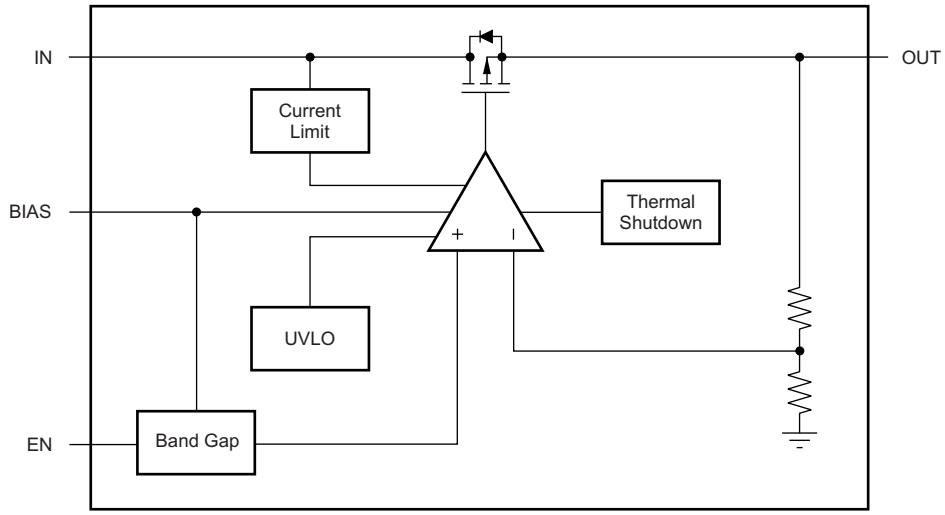
Figure 24. Load Transient Response

7 Detailed Description

7.1 Overview

The TPS720-Q1 family of LDO regulators uses innovative circuitry to achieve ultra-wide bandwidth and high loop gain, resulting in extremely high PSRR (up to 1 MHz) at very low headroom (V_{IN} – V_{OUT}). The implementation of the BIAS pin on the TPS720-Q1 vastly improves efficiency of low V_{OUT} applications by allowing the use of a pre-regulated, low-voltage input supply. The TPS720-Q1 supports a novel feature where the output of the LDO regulates under light loads (< 500 μA) when the IN pin is left floating. The light-load drive current is sourced from V_{BIAS} under this condition. This feature is particularly useful in power-saving applications where the dc-dc converter connected to the IN pin is disabled but the LDO is still required to regulate the voltage to a light load. These features, combined with low noise, low ground pin current, and ultra-small packaging, make this device ideal for portable applications. This family of regulators offers sub-band-gap output voltages, current limit, and thermal protection, and is fully specified from –40°C to +125°C.

7.2 Functional Block Diagram



7.3 Feature Description

7.3.1 Internal Current Limit

The TPS720-Q1 internal current limits help protect the regulator during fault conditions. During current limit, the output sources a fixed amount of current that is largely independent of output voltage. In such a case, the output voltage is not regulated, and is $V_{OUT} = I_{LIMIT} \times R_{LOAD}$. The NMOS pass transistor dissipates (V_{IN} – V_{OUT}) × I_{OUT} until thermal shutdown is triggered and the device is turned off. When the device cools down, the internal thermal shutdown circuit turns the device back on. If the fault condition continues, the device cycles between current limit and thermal shutdown; see *Thermal Considerations* for more details.

The NMOS pass element in the TPS720-Q1 has a built-in body diode that conducts current when the voltage at OUT exceeds the voltage at IN. This current is not limited, so if extended reverse voltage operation is anticipated, TI recommends external limiting to 5% of rated output current.

7.3.2 Inrush Current Limit

The TPS720-Q1 family of LDO regulators implements a novel inrush current limit circuit architecture: the current drawn through the IN pin is limited to a finite value. This $I_{INRUSHLIMIT}$ charges the output to the final voltage. All current drawn through V_{IN} charges the output capacitance when the load is disconnected. Equation 1 shows the inrush current limit performed by the circuit.

$$I_{INRUSHLIMIT}(A) = C_{OUT}(\mu F) \times 0.454545 (V/\mu s) + I_{LOAD}(A) \quad (1)$$

Feature Description (continued)

Assuming a C_{OUT} of 2.2 μF with the load disconnected (that is, I_{LOAD} = 0), the $I_{INRUSHLIMIT}$ is calculated to be 100 mA. The inrush current charges the LDO output capacitor. If the output of the LDO regulates to 1.3 V, then the LDO charges the output capacitor to the final output value in approximately 28.6 μs.

Another consideration is when a load is connected to the output of an LDO. The TPS720-Q1 inrush current limit circuit employs a technique that supplies not only the $I_{INRUSHLIMIT}$, but the additional current required by the load. If I_{LOAD} = 350 mA, then $I_{INRUSHLIMIT}$ calculates to be approximately 450 mA (from Equation 1).

7.3.3 Shutdown

The enable pin (EN) is active high and is compatible with standard and low-voltage, TTL-CMOS levels. When shutdown capability is not required, EN can be connected to the IN pin.

7.3.4 Undervoltage Lockout (UVLO)

The TPS720-Q1 uses an undervoltage lockout circuit on the BIAS pin to keep the output shut off until the internal circuitry is operating properly. The UVLO circuit has a deglitch feature that typically ignores undershoot transients on the input if these transients are less than 50 μs in duration.

7.4 Device Functional Modes

Driving the EN pin over 1.1 V turns on the regulator. Driving the EN pin below 0.4 V causes the regulator to enter shutdown mode. In shutdown, the current consumption of the device is typically reduced to 500 nA.

8 Application and Implementation

NOTE

Information in the following applications sections is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

8.1 Application Information

8.1.1 Input and Output Capacitor Requirements

Although a capacitor is not required for stability on the IN pin, good analog design practice is to connect a 0.1-μF to 1-μF low equivalent series resistance (ESR) capacitor across the IN pin input supply near the regulator. This capacitor counteracts reactive input sources and improves transient response, noise rejection, and ripple rejection. A higher-value capacitor may be necessary if large, fast rise-time load transients are anticipated, or if the device is located far from the power source. If source impedance is not sufficiently low, a 0.1-μF input capacitor may be necessary to ensure stability.

The BIAS pin does not require an input capacitor because BIAS does not source high currents. However, if source impedance is not sufficiently low, TI recommends a small 0.1-μF bypass capacitor.

The TPS720-Q1 is designed to be stable with standard ceramic capacitors with values of 2.2 μF or larger at the output. X5R- and X7R-type capacitors are best because they have minimal variation in value and ESR over temperature. Maximum ESR must be less than 250 mΩ.

8.1.2 Output Regulation With the IN Pin Floating

The TPS720-Q1 supports a novel feature where the output of the LDO regulates under light loads when the IN pin is left floating. Under normal conditions when the IN pin is connected to a power source, the BIAS pin draws only tens of milliamperes. However, when the IN pin is floating, an innovative circuit allows a maximum current of 500 μA to be drawn by the load through the BIAS pin and maintains the output in regulation. This feature is particularly useful in power-saving applications where a dc-dc converter connected to the IN pin is disabled, but the LDO is required to regulate the output voltage to a light load.

Figure 25 shows an application example where a microcontroller is not turned off (to maintain the state of the internal memory), but where the regulated supply (shown as the TPS62xxx) is turned off to reduce power. In this case, the TPS720-Q1 BIAS pin provides sufficient load current to maintain a regulated voltage to the microcontroller.

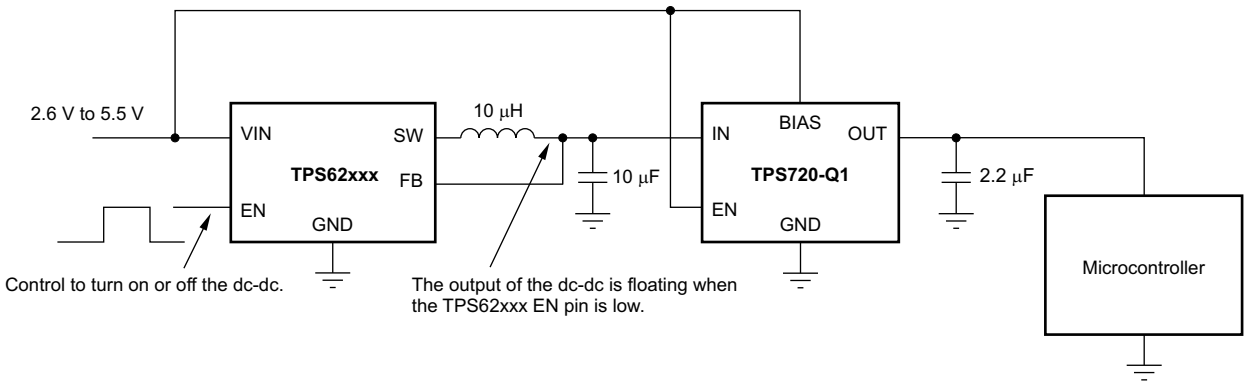


Figure 25. Floating IN Pin Regulation Example

Application Information (continued)

8.1.3 Dropout Voltage

The TPS720-Q1 uses a NMOS pass transistor to achieve low dropout. When (V_{IN} – V_{OUT}) is less than the dropout voltage (V_{DO}), the NMOS pass device is in the linear region of operation and the input-to-output resistance is the $R_{DS(ON)}$ of the NMOS pass element. V_{DO} approximately scales with output current because the NMOS device behaves like a resistor in dropout.

PSRR and transient response are degraded when (V_{IN} – V_{OUT}) approaches dropout. This effect is shown in Figure 19.

8.1.4 Transient Response

Increasing the size of the output capacitor reduces overshoot and undershoot magnitude but increases duration of the transient response.

8.1.5 Minimum Load

The TPS720-Q1 is stable with no output load. Although some LDOs suffer from low loop gain at very light output loads, the TPS720-Q1 employs an innovative, low-current mode circuit under very light or no-load conditions which improves output voltage regulation performance.

8.2 Typical Application

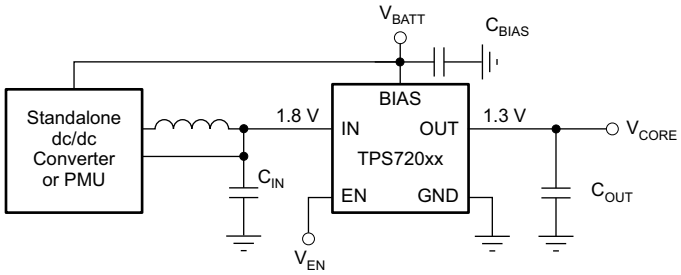


Figure 26. Typical Application Schematic

8.2.1 Design Requirements

Table 1 lists the parameters for this design example.

Table 1. Design Parameters

DESIGN PARAMETER	EXAMPLE VALUE
V_{IN}	2.3 V
V_{BIAS}	3.2 V
V_{OUT}	1.8 V
I_{OUT}	10-mA typical, 350-mA peak

8.2.2 Detailed Design Procedures

TI recommends selecting the minimum component size; a small size solution for this design example is desired. Set C_{IN} = 1 µF, C_{BIAS} = 100 nF, and C_{OUT} = 2.2 µF.

8.2.3 Application Curves

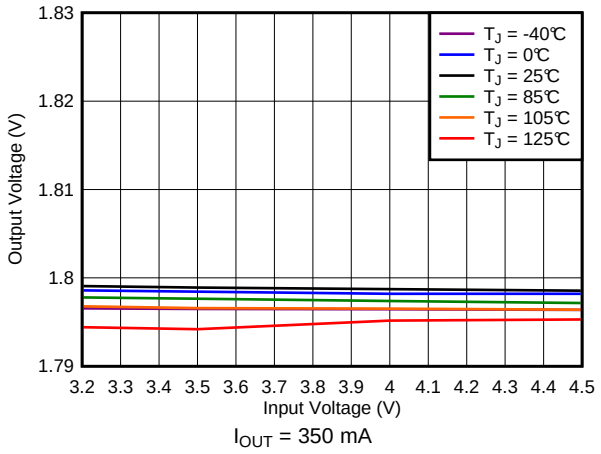


Figure 27. V_{IN} Line Regulation

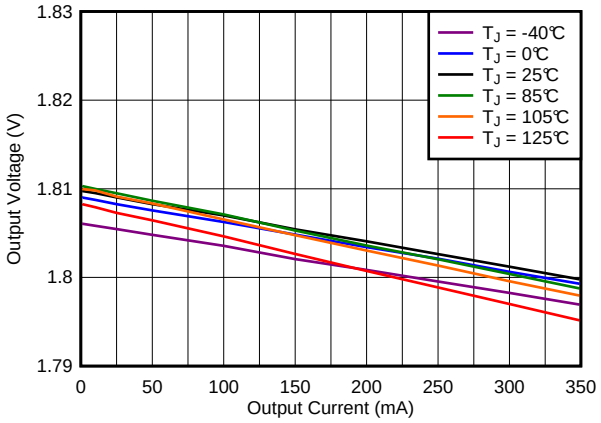


Figure 28. Load Regulation

9 Power Supply Recommendations

The input supply and bias supply for the LDO must be within the recommended operating conditions and must provide adequate headroom for the device to have a regulated output. The minimum capacitor requirements must be met, and if the input supply is noisy, additional input capacitors with low ESR can improve transient performance.

10 Layout

10.1 Layout Guidelines

TI recommends designing the board with separate ground planes for V_{IN} and V_{OUT}, with the ground plane connected only at the GND pin of the device to improve ac performance (such as PSRR, output noise, and transient response.) In addition, the ground connection for the output capacitor must be connected directly to the GND pin of the device. High equivalent series resistance (ESR) capacitors can degrade PSRR. The BIAS pin draws very little current and can be routed as a signal. Take care to shield the BIAS pin from high frequency coupling.

10.2 Layout Example

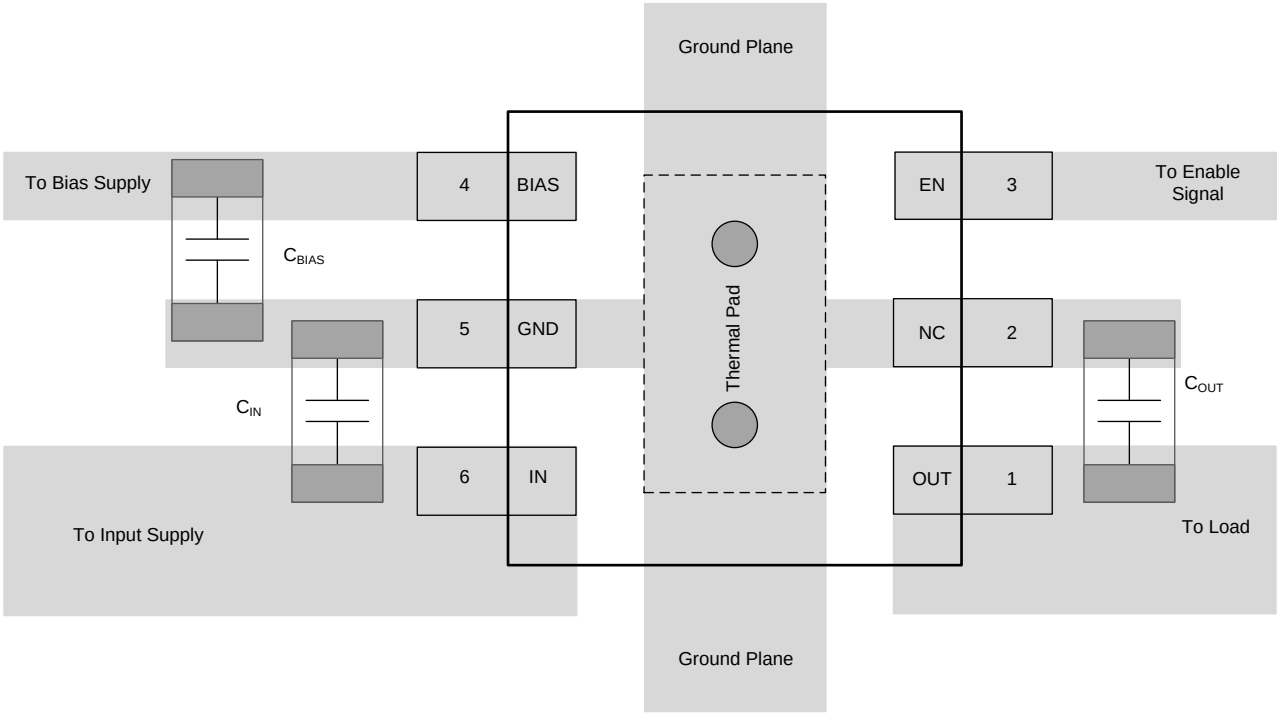


Figure 29. Recommended Layout

10.3 Thermal Considerations

Thermal protection disables the output when the junction temperature rises to approximately +160°C, allowing the device to cool. When the junction temperature cools to approximately +140°C, the output circuitry is again enabled. Depending on power dissipation, thermal resistance, and ambient temperature, the thermal protection circuit can cycle on and off. This cycling limits the dissipation of the regulator, protecting the regulator from damage as a result of overheating.

Any tendency to activate the thermal protection circuit indicates excessive power dissipation or an inadequate heat sink. For reliable operation, limit junction temperature to a maximum of +125°C. To estimate the margin of safety in a complete design (including heat sink), increase the ambient temperature until the thermal protection is triggered; use worst-case loads and signal conditions. For good reliability, trigger thermal protection at least 35°C above the maximum expected ambient condition of the particular application. This configuration produces a worst-case junction temperature of +125°C at the highest expected ambient temperature and worst-case load.

The internal protection circuitry of the TPS720-Q1 is designed to protect against overload conditions. This circuitry is not intended to replace proper heat sinking. Continuously running the TPS720-Q1 into thermal shutdown degrades device reliability.

10.4 Power Dissipation

The printed-circuit-board (PCB) area around the device that is free of other components moves the heat from the device to ambient air. Performance data for JEDEC boards are given in the *Thermal Information* table. Using heavier copper increases the effectiveness in removing heat from the device. The addition of plated through-holes to heat-dissipating layers also improves the heat sink effectiveness.

Power dissipation depends on input voltage and load conditions. Power dissipation (P_D) is equal to the product of the output current times the voltage drop across the output pass element (V_{IN} to V_{OUT}), as shown in Equation 2:

$$P_D = (V_{IN} - V_{OUT}) \times I_{OUT} \quad (2)$$

11 器件和文档支持

11.1 器件支持

11.1.1 开发支持

11.1.1.1 评估模块

评估模块 (EVM) 可与 TPS720-Q1 配套使用，帮助评估初始电路性能。TPS720xxDRVEVM 评估模块（和相关用户指南）可在德州仪器 (TI) 网站上的产品文件夹中获取，也可直接从 TI 网上商店购买。

的表注中的输出电压范围从“0.9V 至 3.0V”更改为“0.9V 至 3.3V”

11.1.2 器件命名规则

表 **2.** 器件命名规则 (1) (2)

产品	V_{OUT}
TPS720**xx(x)**Q**yyyz**Q1	**xx(x)** 为标称输出电压。对于分辨率为 100mV 的输出电压，订货编号中使用两位数字；否则，使用三位数字（例如，28 = 2.8V；125 = 1.25V）。 **yyy** 为封装标识符。 **z** 为封装数量。R 表示 3000 片，T 表示 250 片。

(1) 要获得最新的封装和订货信息，请参见本文档末尾的封装选项附录，或者访问器件产品文件夹（www.ti.com.cn）。
(2) 可提供 0.9V 至 3.3V 范围内的输出电压（以 50mV 为单位增量）。更多详细信息及可用性，请联系制造商。

11.2 文档支持

11.2.1 相关文档

相关文档如下：

- *《高效降压低功耗 DC-DC 转换器》*（文献编号：SGLS243）。
- *《TPS720xxDRVEVM 评估模块》*（文献编号：SBVU024）。
- *《使用新的热指标》*（文献编号：SBVA025）。

11.3 接收文档更新通知

如需接收文档更新通知，请访问 www.ti.com.cn 网站上的器件产品文件夹。点击右上角的*提醒我* (Alert me) 注册后，即可每周定期收到已更改的产品信息。有关更改的详细信息，请查阅已修订文档中包含的修订历史记录。

11.4 社区资源

The following links connect to TI community resources. Linked contents are provided "AS IS" by the respective contributors. They do not constitute TI specifications and do not necessarily reflect TI's views; see TI's Terms of Use.

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Design Support ***TI's Design Support*** Quickly find helpful E2E forums along with design support tools and contact information for technical support.

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ESD 的损坏小至导致微小的性能降级，大至整个器件故障。 精密的集成电路可能更容易受到损坏，这是因为非常细微的参数更改都可能会导致器件与其发布的规格不相符。

11.7 Glossary

SLYZ022 — *TI Glossary*.

This glossary lists and explains terms, acronyms, and definitions.

12 机械、封装和可订购信息

以下页中包括机械、封装和可订购信息。这些信息是针对指定器件可提供的最新数据。这些数据会在无通知且不对本文档进行修订的情况下发生改变。欲获得该数据表的浏览器版本，请查阅左侧的导航栏。

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PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material (6)	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
TPS72009QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	11P	Samples
TPS720105QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	15G	Samples
TPS72010QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	11Q	Samples
TPS720115QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	15H	Samples
TPS72011QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	11I	Samples
TPS72012QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	11R	Samples
TPS72015QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	11J	Samples
TPS72018QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	11K	Samples
TPS72025QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	11W	Samples
TPS72027QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	15I	Samples
TPS720285QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	11M	Samples
TPS72028QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	11L	Samples
TPS72029QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	11N	Samples
TPS72030QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	11O	Samples
TPS72033QDRVRQ1	ACTIVE	WSON	DRV	6	3000	RoHS & Green	NIPDAU	Level-1-260C-UNLIM	-40 to 125	15J	Samples

(1) The marketing status values are defined as follows:
ACTIVE: Product device recommended for new designs.
LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.
NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.
PREVIEW: Device has been announced but is not in production. Samples may or may not be available.
OBSOLETE: TI has discontinued the production of the device.

(2) RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".
RoHS Exempt: TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.
Green: TI defines "Green" to mean the content of Chlorine (Cl) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

(3) MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

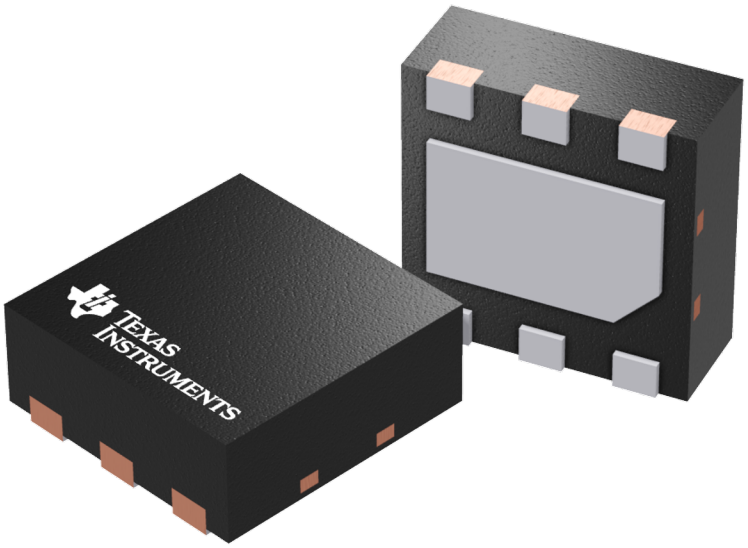
(4) There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

(5) Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

(6) Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

DRV 6 WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



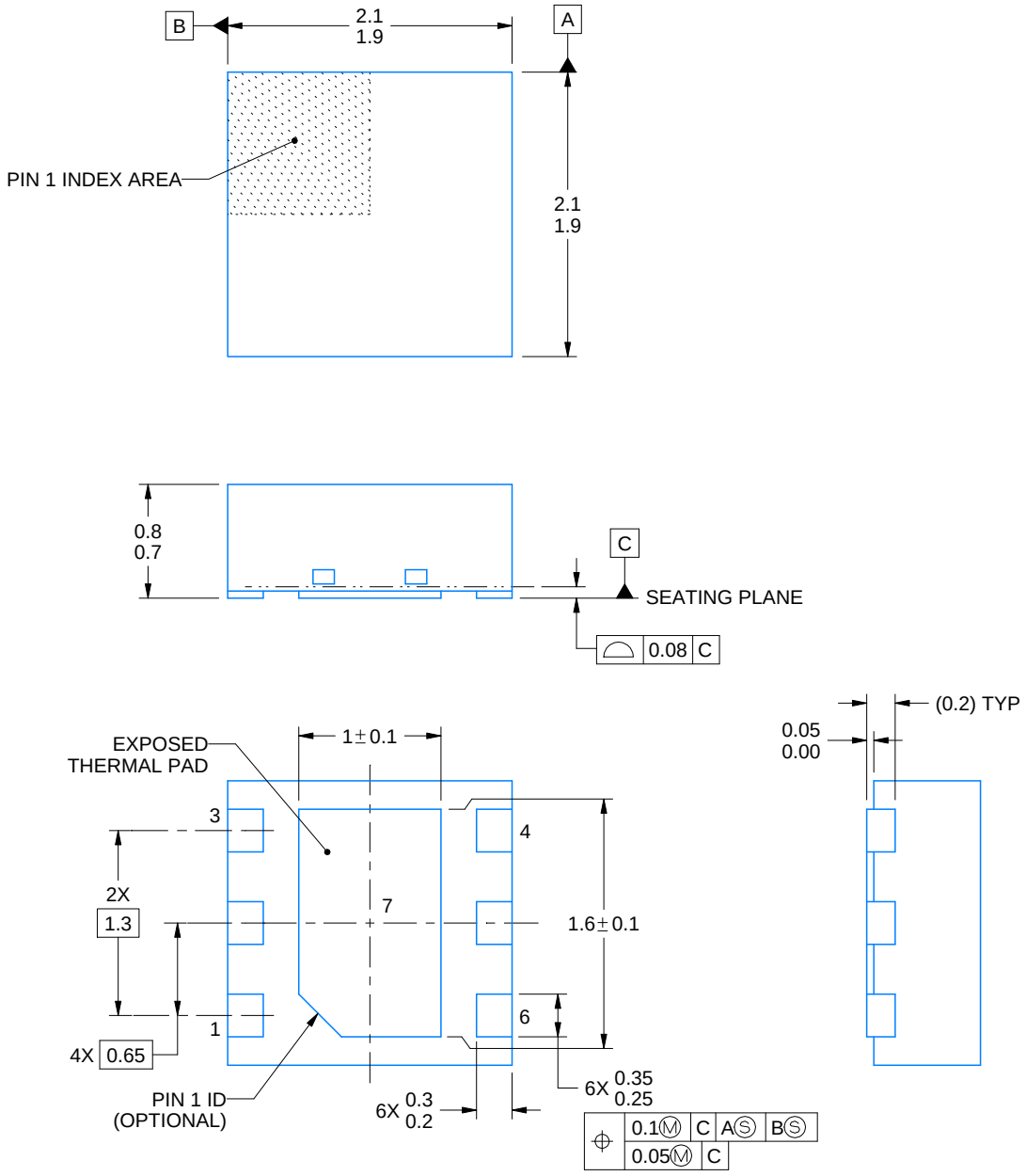
Images above are just a representation of the package family, actual package may vary.
Refer to the product data sheet for package details.

PACKAGE OUTLINE

DRV0006A

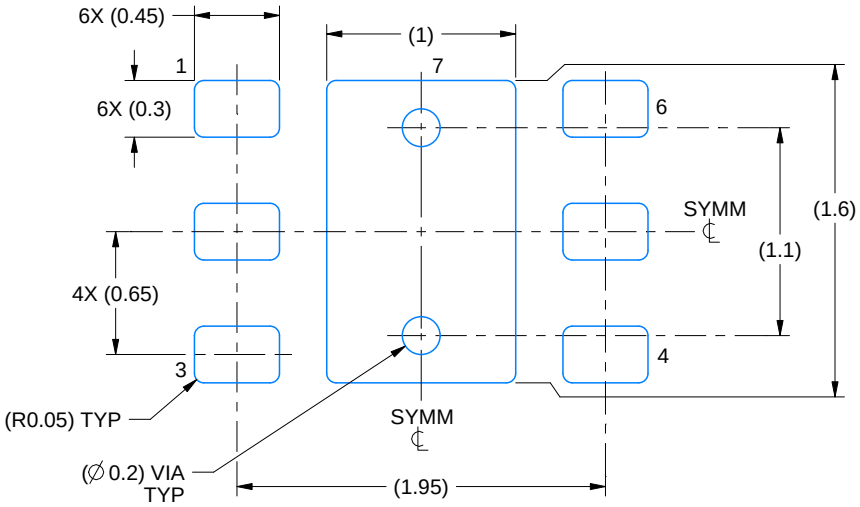
WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD

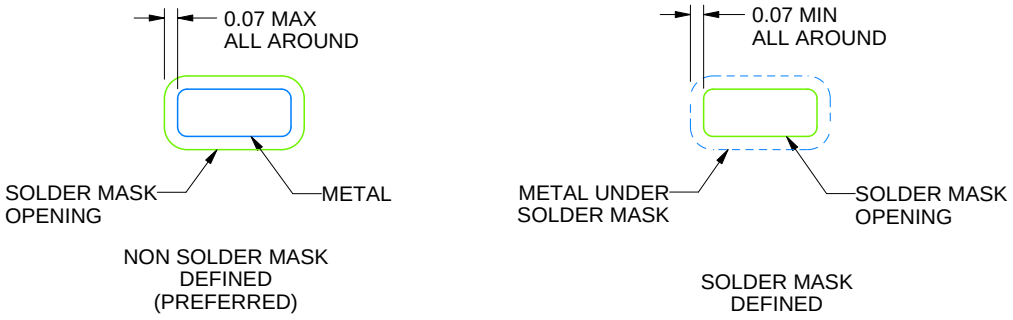


NOTES:

1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
2. This drawing is subject to change without notice.
3. The package thermal pad must be soldered to the printed circuit board for thermal and mechanical performance.



LAND PATTERN EXAMPLE
SCALE:25X



SOLDER MASK DETAILS

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NOTES: (continued)

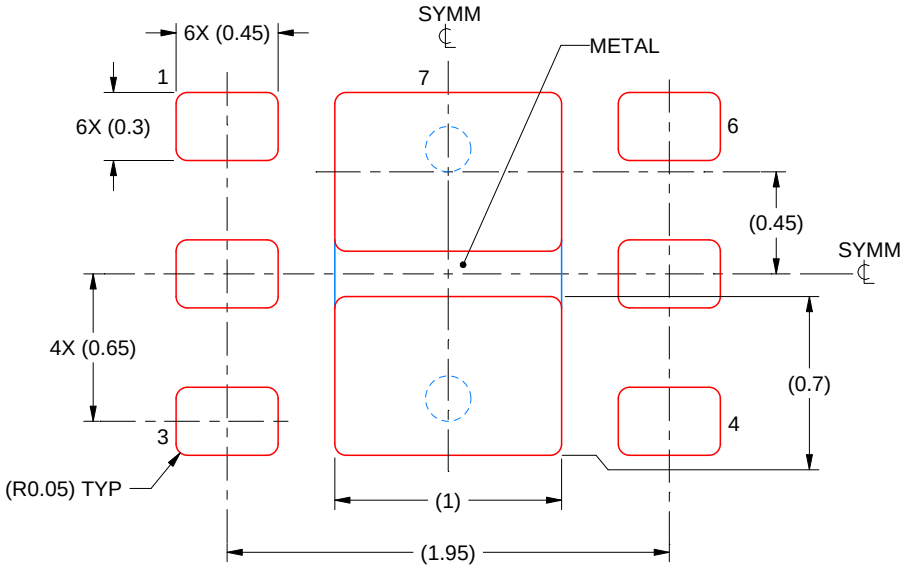
4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
5. Vias are optional depending on application, refer to device data sheet. If some or all are implemented, recommended via locations are shown.

EXAMPLE STENCIL DESIGN

DRV0006A

WSON - 0.8 mm max height

PLASTIC SMALL OUTLINE - NO LEAD



SOLDER PASTE EXAMPLE
BASED ON 0.125 mm THICK STENCIL

EXPOSED PAD #7
88% PRINTED SOLDER COVERAGE BY AREA UNDER PACKAGE
SCALE:30X

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NOTES: (continued)

6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.

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